

E Series Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V) at T_J max.	650
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V 0.6
Q_g max. (nC)	40
Q_{gs} (nC)	5
Q_{gd} (nC)	9
Configuration	Single

FEATURES

- Low Figure-of-Merit (FOM) $R_{on} \times Q_g$
- Low Input Capacitance (C_{iss})
- Reduced Switching and Conduction Losses
- Ultra Low Gate Charge (Q_g)
- Avalanche Energy Rated (UIS)
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

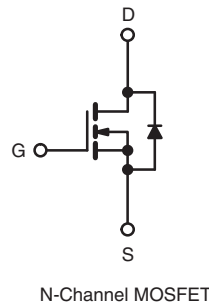
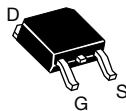


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Server and Telecom Power Supplies
- Switch Mode Power Supplies (SMPS)
- Power Factor Correction Power Supplies (PFC)
- Lighting
 - High-Intensity Discharge (HID)
 - Fluorescent Ballast Lighting
- Industrial
 - Welding
 - Induction Heating
 - Motor Drives
 - Battery Chargers
 - Renewable Energy
 - Solar (PV Inverters)

DDPAK
(TO-252)




ORDERING INFORMATION	
Package	DDPAK (TO-252)
Lead (Pb)-free and Halogen-free	SiHD7N60E-GE3
	SiHD7N60ET1-GE3
	SiHD7N60ET5-GE3
	SiHD7N60ET4-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	600	V
Drain-Source Voltage		$T_C = -25$ °C, $I_D = 250$ μ A	
Gate-Source Voltage	V_{GS}	± 20	
Gate-Source Voltage AC ($f > 1$ Hz)		30	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current ^a	I_{DM}	18	
Linear Derating Factor		0.63	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	43	mJ
Maximum Power Dissipation	P_D	78	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	°C
Drain-Source Voltage Slope	dV/dt	$T_J = 125$ °C	37
Reverse Diode dV/dtd		3	
Soldering Recommendations (Peak Temperature) ^c		for 10 s	300
			°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 13.8$ mH, $R_g = 25$ Ω , $I_{AS} = 2.5$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.6	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		609	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$		-	0.68	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2	-	4	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	μA
		$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 3.5\text{ A}$	-	0.5	0.6	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 3.5\text{ A}$		-	1.9	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 100\text{ V},$ $f = 1\text{ MHz}$		-	680	-	pF
Output Capacitance	C_{oss}			-	39	-	
Reverse Transfer Capacitance	C_{rss}			-	5	-	
Effective Output Capacitance, Energy Related ^a	$C_{o(er)}$			-	34	-	
Effective Output Capacitance, Time Related ^b	$C_{o(tr)}$	$V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$		-	100	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 3.5\text{ A}, V_{DS} = 480\text{ V}$	-	20	40	nC
Gate-Source Charge	Q_{gs}			-	5	-	
Gate-Drain Charge	Q_{gd}			-	9	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 480\text{ V}, I_D = 3.5\text{ A},$ $V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$		-	13	26	ns
Rise Time	t_r			-	13	26	
Turn-Off Delay Time	$t_{d(off)}$			-	24	48	
Fall Time	t_f			-	14	28	
Gate Input Resistance	R_g	$f = 1\text{ MHz}, \text{ open drain}$		-	1.1	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	7	A
Pulsed Diode Forward Current	I_{SM}			-	-	18	
Diode Forward Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 3.5\text{ A}, V_{GS} = 0\text{ V}$		-	-	1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 3.5\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s}, V_R = 20\text{ V}$		-	230	-	ns
Reverse Recovery Charge	Q_{rr}			-	1.9	-	μC
Reverse Recovery Current	I_{RRM}			-	14	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
 b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

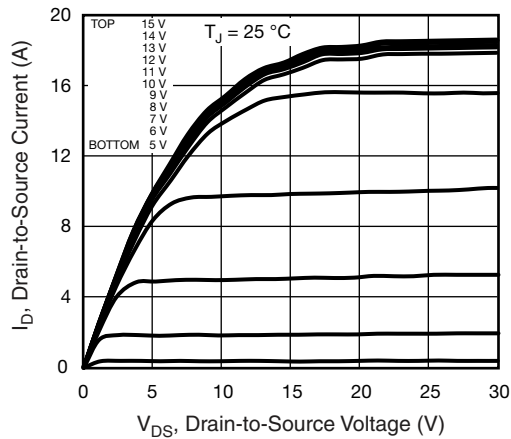


Fig. 1 - Typical Output Characteristics

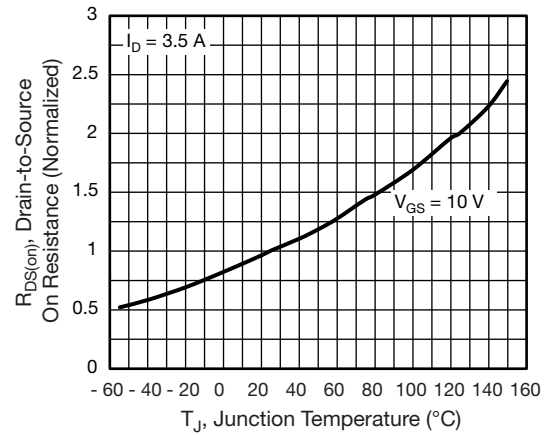


Fig. 4 - Normalized On-Resistance vs. Temperature

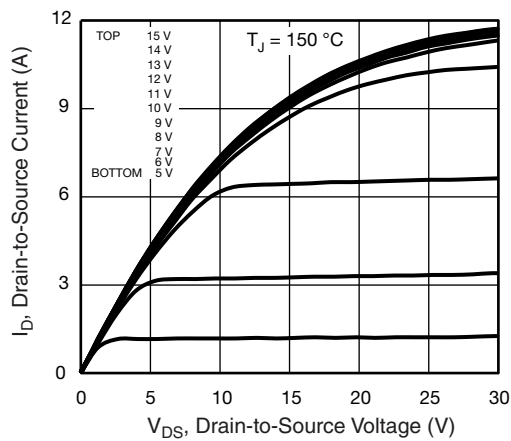


Fig. 2 - Typical Output Characteristics

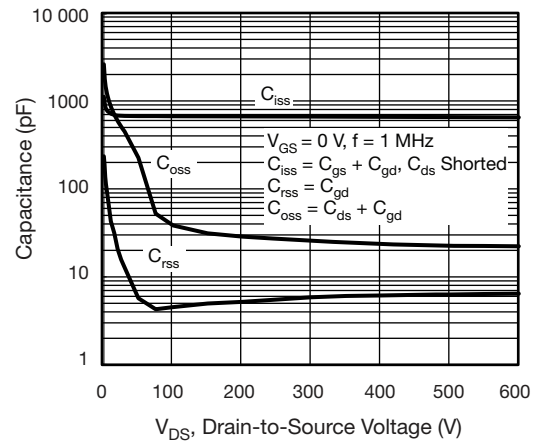


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

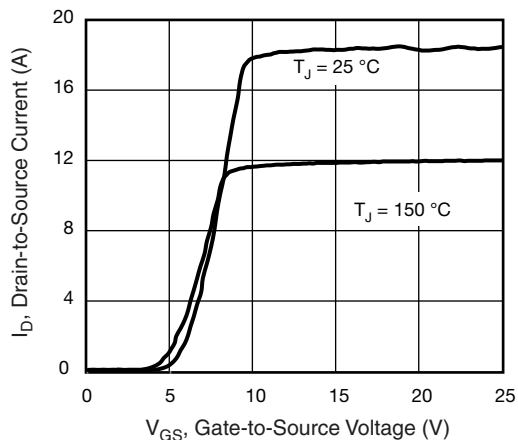


Fig. 3 - Typical Transfer Characteristics

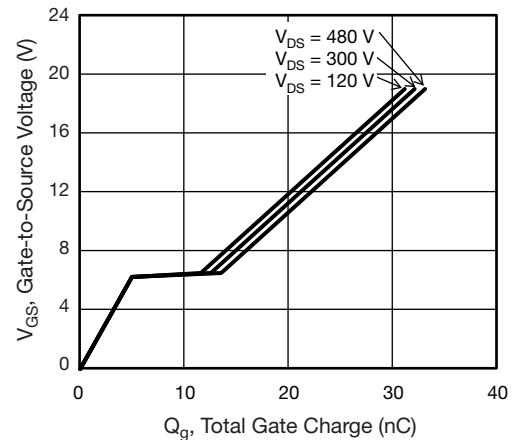


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

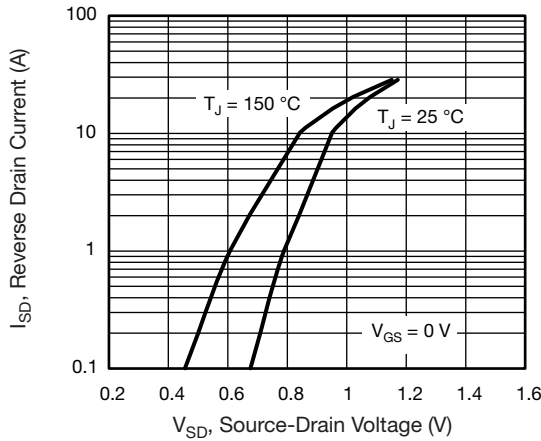


Fig. 7 - Typical Source-Drain Diode Forward Voltage

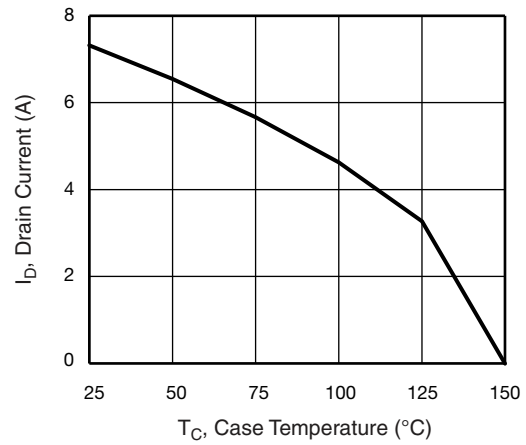


Fig. 9 - Maximum Drain Current vs. Case Temperature

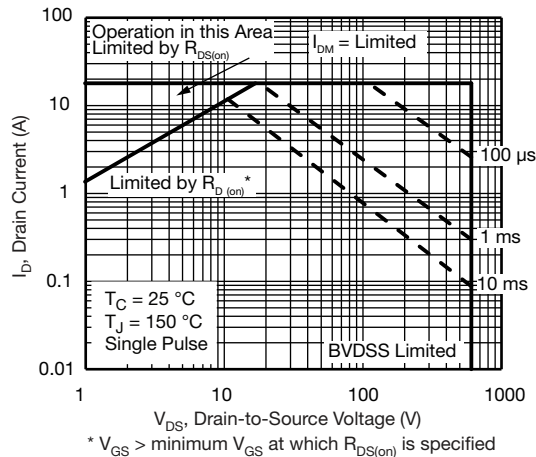


Fig. 8 - Maximum Safe Operating Area

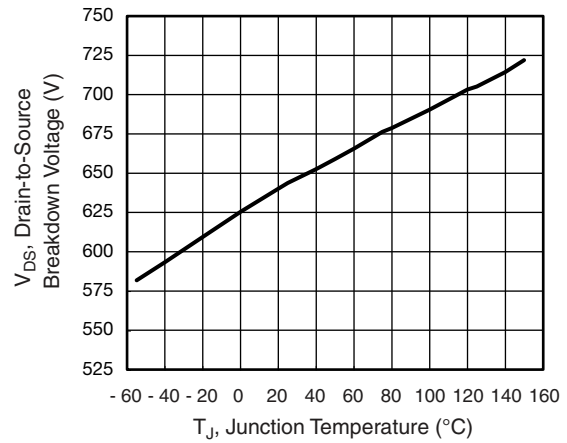


Fig. 10 - Temperature vs. Drain-to-Source Voltage

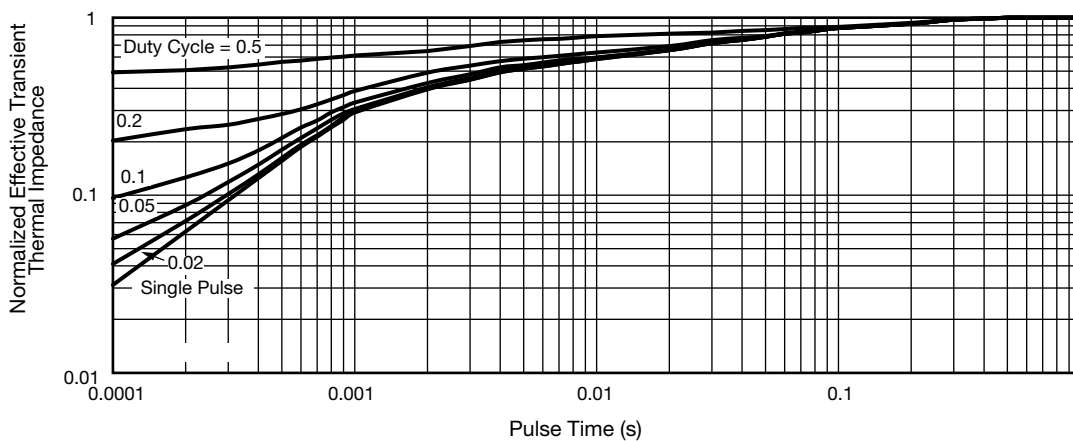


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

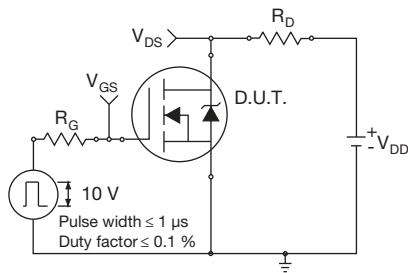


Fig. 12 - Switching Time Test Circuit

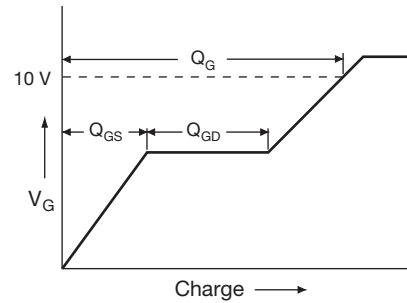


Fig. 16 - Basic Gate Charge Waveform

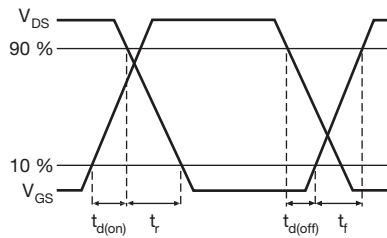


Fig. 13 - Switching Time Waveforms

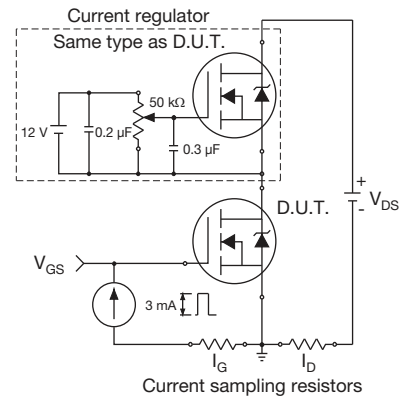


Fig. 17 - Gate Charge Test Circuit

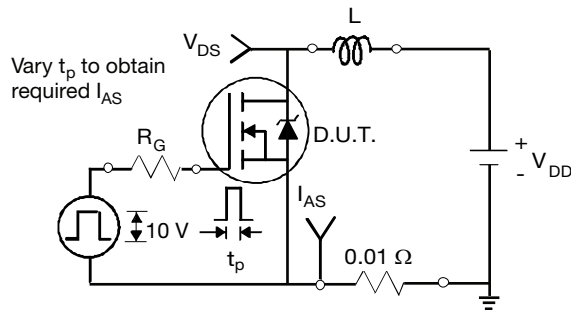


Fig. 14 - Unclamped Inductive Test Circuit

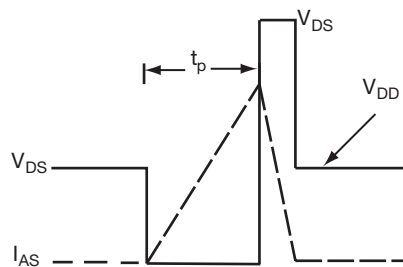
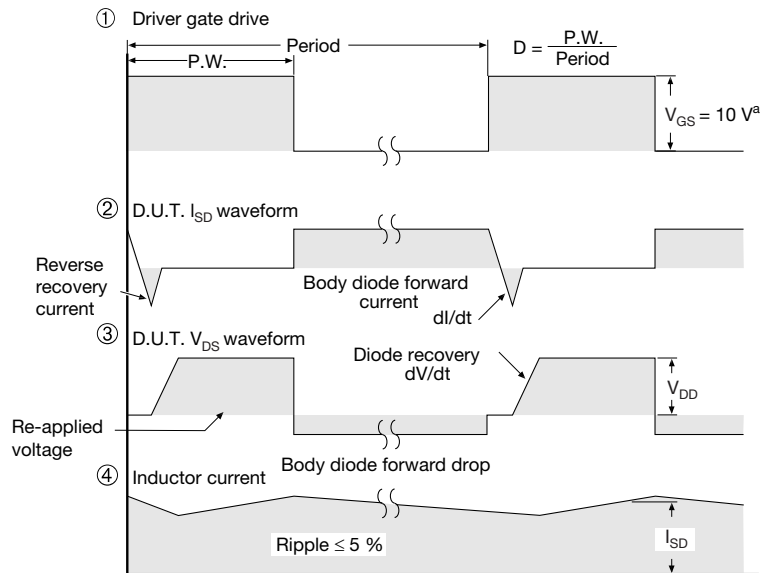
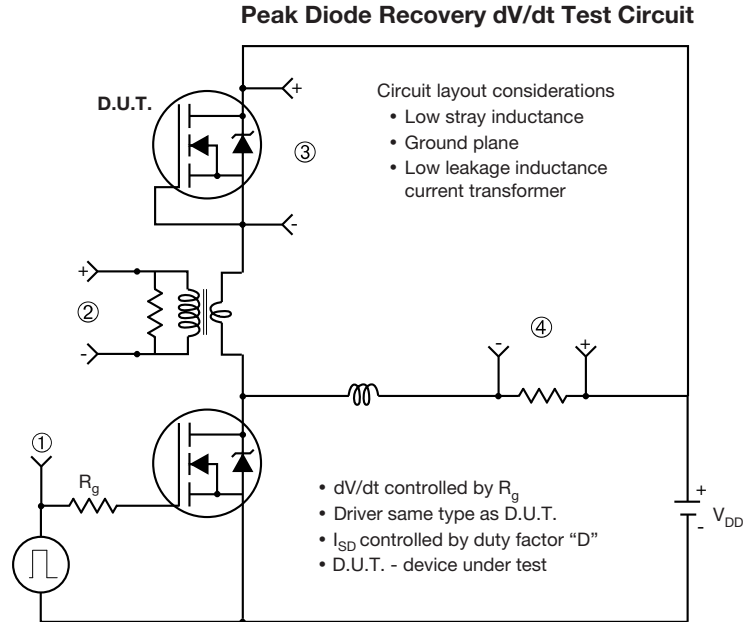


Fig. 15 - Unclamped Inductive Waveforms



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 18 - For N-Channel

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TO-252AA Case Outline

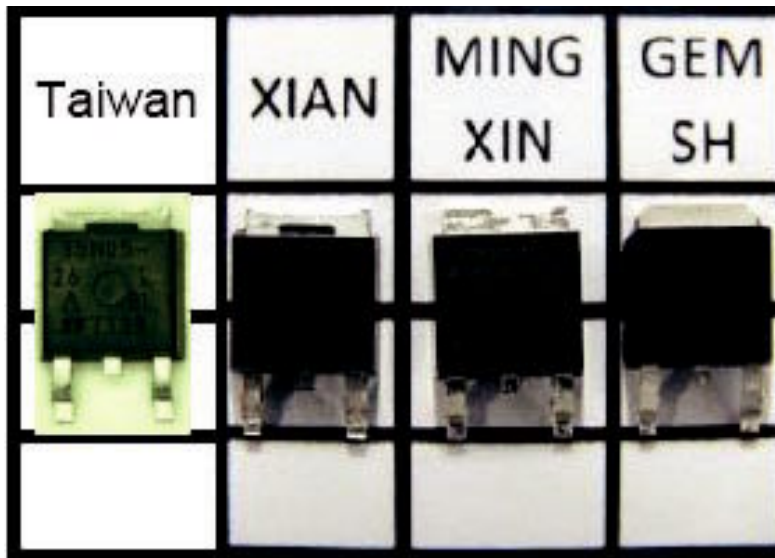


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060

ECN: T13-0359-Rev. O, 03-Jun-13
DWG: 5347

Notes

- Dimension L3 is for reference only.
- Xi'an, Mingxin, and GEM SH actual photo.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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